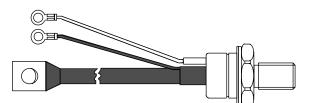




Vishay High Power Products

Phase Control Thyristors (Stud Version), 110 A



TO-209AC (TO-94)

PRODUCT SUMMARY	
I _{T(AV)}	110 A

FEATURES

- High current and high surge ratings
- Hermetic ceramic housing
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level



TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		110	А		
I _{T(AV)}	T _C	90	°C		
I _{T(RMS)}		172			
	50 Hz	2080	А		
I _{TSM}	60 Hz	2180			
I2t	50 Hz	21.7	kA ² s		
1-1	60 Hz	19.8	KA-S		
V _{DRM} /V _{RRM}		400 to 1200	V		
t _q	Typical	110	μѕ		
T _J		- 40 to 140	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA		
	40	400	500			
110RKI 111RKI	80	800	900	20		
	120	1200	1300			



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PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave		110	A °C	
·		DO 100 00			90	ڼ
Maximum RMS on-state current	I _{T(RMS)}	DC at 83 °C	case temperat	ure -	172	
		t = 10 ms	No voltage		2080	
Maximum peak, one-cycle	ı	t = 8.3 ms	reapplied		2180	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	ms 100 % V _{RRM}		1750	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1830	
Maximum I ² t for fusing		t = 10 ms	No voltage reapplied	initial T _J = T _J maximum	21.7	
	l ² t	t = 8.3 ms			19.8	
		t = 10 ms	100 % V _{RBM}		15.3	
		t = 8.3 ms	reapplied		14.0	
Maximum I²√t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied		217	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.82	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.02	V	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		2.16	0	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.70	mΩ	
Maximum on-state voltage	V_{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$		1.57	V	
Maximum holding current	I _H	T 05.00		Maradalla da ad	200	
Typical latching current	ΙL	T _J = 25 °C, anode supply 6 V resistive load		400	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	300	A/μs
Typical delay time	t _d	Gate current 1 A, $d_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1	
Typical turn-off time	t _q	I_{TM} = 50 A, T_J = T_J maximum, dI/dt = - 5 A/μs V_R = 50 V, dV/dt = 20 V/μs, gate 0 V 25 Ω	110	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA



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TRIGGERING						
PARAMETER	SYMBOL	TEST	TEST CONDITIONS		VALUES	
PANAMETEN	STIMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	12		w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0] *v
Maximum peak positive gate current	I _{GM}			3.0		Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	2	0	V
Maximum peak negative gate voltage	- V _{GM}		1	0]	
DC gate current required to trigger		T _J = - 40 °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	
	I _{GT}	T _J = 25 °C		80	120	mA
		T _J = 140 °C		40	-	
		T _J = - 40 °C		2.5	-	V
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C		1.6	2	
		T _J = 140 °C		1	-	
DC gate current not to trigger	I _{GD}	$T_J = T_J \text{maximum}$ Maximum gate current/ voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied		6.0		mA
DC gate voltage not to trigger	V _{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		- 40 to 140	°C	
Maximum storage temperature range	T _{Stg}		- 40 to 150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.27	K/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1	r/ VV	
Mounting torque 10.0/		Non-lubricated threads	15.5 (137)	N⋅m	
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet TO-209AC (TO-94)		C (TO-94)	

∆R _{thJC} CONDUCTIO	N			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.043	0.031		
120°	0.052	0.053		
90°	0.066	0.071	$T_J = T_J$ maximum	K/W
60°	0.096	0.101		
30°	0.167	0.169		

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

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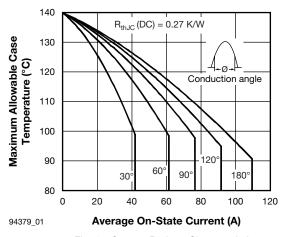


Fig. 1 - Current Ratings Characteristics

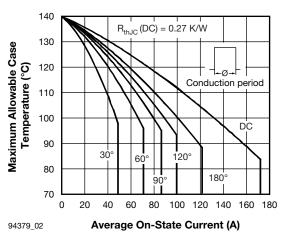
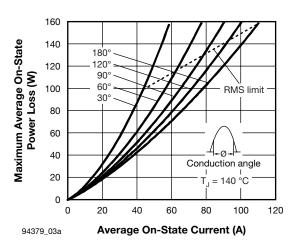


Fig. 2 - Current Ratings Characteristics



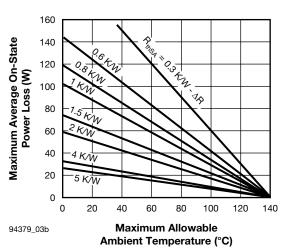
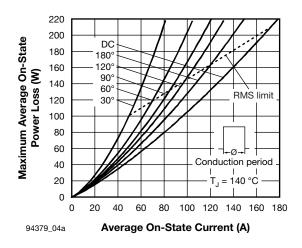


Fig. 3 - On-State Power Loss Characteristics



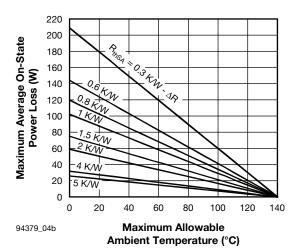


Fig. 4 - On-State Power Loss Characteristics





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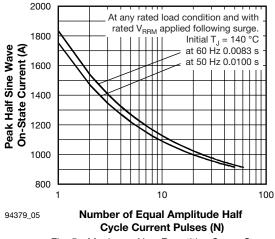


Fig. 5 - Maximum Non-Repetitive Surge Current

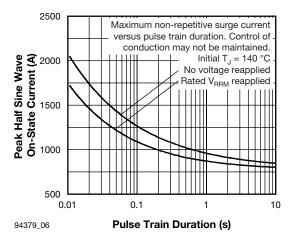


Fig. 6 - Maximum Non-Repetitive Surge Current

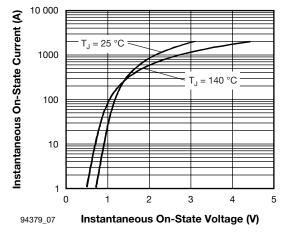


Fig. 7 - On-State Voltage Drop Characteristics

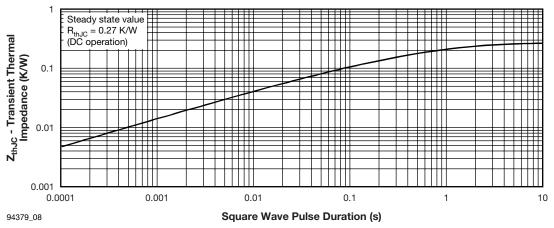
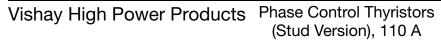


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic





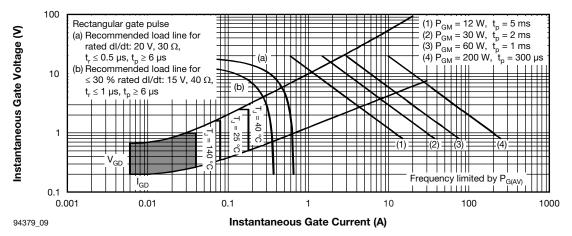
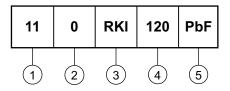


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 I_{T(AV)} rated average output current (rounded/10)
- 0 = Eyelet terminals (gate and auxiliary cathode leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode leads)
- 3 Thyristo
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 5 None = Standard production
 - PbF = Lead (Pb)-free

LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95003





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